

N-channel 80 V, 4.3 mΩ standard level MOSFET in TO220 Rev. 03 — 18 April 2011 Product data

Product data sheet

Product profile 1.

1.1 General description

Standard level N-channel MOSFET in TO220 package qualified to 175C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive

1.3 Applications

- DC-to-DC converters
- Load switch

- Motor control
- Server power supplies

1.4 Quick reference data

Table 1. **Quick reference data**

Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	80	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; see <u>Figure 1</u>	<u>[1]</u>	-	-	120	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	-	306	W
Tj	junction temperature			-55	-	175	°C
Static cha	racteristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 ^\circ\text{C}; \text{ see } \frac{\text{Figure } 13}{100000000000000000000000000000000000$	[2]	-	3.7	4.3	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _i = 100 °C; see Figure 12	[2]	-	6.1	7.1	mΩ



N-channel 80 V, 4.3 m Ω standard level MOSFET in TO220

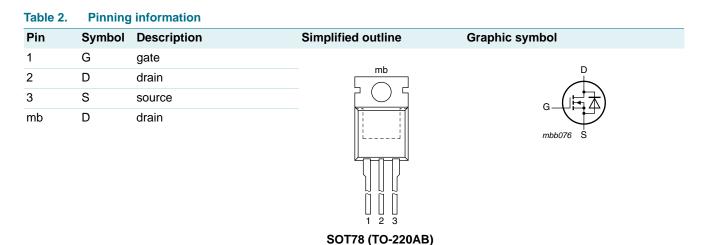
 Table 1.
 Quick reference data ...continued

Quion reference dut					
Parameter	Conditions	Min	Тур	Max	Unit
characteristics					
gate-drain charge	V _{GS} = 10 V; I _D = 75 A;	-	28.4	-	nC
total gate charge	V _{DS} = 40 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	111	-	nC
e ruggedness					
non-repetitive drain-source avalanche energy	$ \begin{array}{l} V_{GS} = 10 \; V; \; T_{j(\text{init})} = 25 \; ^{\circ}\text{C}; \\ I_{D} = 120 \; A; \; V_{sup} \leq 80 \; V; \\ R_{GS} = 50 \; \Omega; \; \text{unclamped} \end{array} $	-	-	676	mJ
	Parameter characteristics gate-drain charge total gate charge e ruggedness non-repetitive drain-source	characteristicsgate-drain charge $V_{GS} = 10 \text{ V}; \text{ I}_D = 75 \text{ A};$ total gate charge $V_{DS} = 40 \text{ V}; \text{ see } Figure 14;$ see Figure 15see Figure 15e ruggedness $V_{GS} = 10 \text{ V}; \text{ T}_{j(init)} = 25 \text{ °C};$ non-repetitive $V_{GS} = 10 \text{ V}; \text{ T}_{yuinit} = 25 \text{ °C};$ drain-source $I_D = 120 \text{ A}; \text{ V}_{sup} \leq 80 \text{ V};$	ParameterConditionsMincharacteristicsgate-drain charge $V_{GS} = 10 \text{ V}; I_D = 75 \text{ A};$ $V_{DS} = 40 \text{ V}; see Figure 14;$ see Figure 15-total gate charge $V_{GS} = 40 \text{ V}; see Figure 14;$ see Figure 15-e ruggedness-non-repetitive drain-source $V_{GS} = 10 \text{ V}; \text{ T}_{j(init)} = 25 \text{ °C};$ $I_D = 120 \text{ A}; V_{sup} \le 80 \text{ V};$	ParameterConditionsMinTypcharacteristicsgate-drain charge $V_{GS} = 10 \text{ V}; I_D = 75 \text{ A};$ -28.4total gate charge $V_{DS} = 40 \text{ V};$ see Figure 14; see Figure 15-111e ruggednessnon-repetitive drain-source $V_{GS} = 10 \text{ V}; T_{j(init)} = 25 \text{ °C};$ $I_D = 120 \text{ A}; V_{sup} \le 80 \text{ V};$	ParameterConditionsMinTypMaxcharacteristicsgate-drain charge $V_{GS} = 10 \text{ V}; I_D = 75 \text{ A};$ -28.4-total gate charge $V_{DS} = 40 \text{ V};$ see Figure 14; see Figure 15-111-e ruggedness $V_{GS} = 10 \text{ V}; T_{j(init)} = 25 \text{ °C};$ drain-source-676

[1] Continuous current is limited by package

[2] Measured 3 mm from package.

2. Pinning information



3. Ordering information

Table 3. Ordering information

Type number	Package			
	Name	Description	Version	
PSMN4R3-80PS	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78	

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

		Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	80	V
V _{DGR}	drain-gate voltage	T _j ≥ 25 °C; T _j ≤ 175 °C; R _{GS} = 20 kΩ		-	80	V
V _{GS}	gate-source voltage			-20	20	V
I _D	drain current	V_{GS} = 10 V; T_{mb} = 100 °C; see <u>Figure 1</u>	[1]	-	120	А
		V_{GS} = 10 V; T_{mb} = 25 °C; see <u>Figure 1</u>	[1]	-	120	А
I _{DM}	peak drain current	pulsed; t _p ≤ 10 µs; T _{mb} = 25 °C; see <u>Figure 3</u>		-	688	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	306	W
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T _{sld(M)}	peak soldering temperature			-	260	°C
Source-drain	diode					
I _S	source current	T _{mb} = 25 °C	[1]	-	120	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	688	А
Avalanche ru	Iggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\label{eq:VGS} \begin{array}{l} V_{GS} = 10 \; V; \; T_{j(init)} = 25 \; ^{\circ}C; \; I_D = 120 \; A; \\ V_{sup} \leq 80 \; V; \; R_{GS} = 50 \; \Omega; \; unclamped \end{array}$		-	676	mJ

[1] Continuous current is limited by package

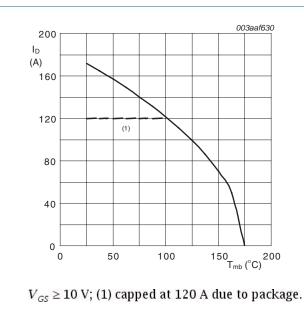
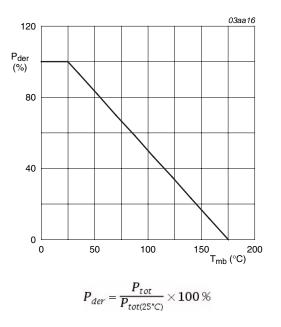
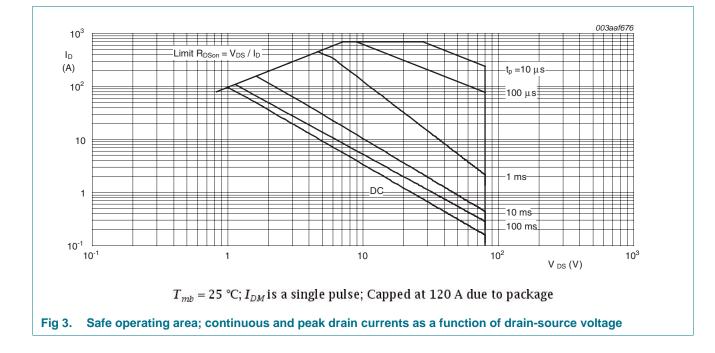


Fig 1. Continuous drain current as a function of mounting base temperature





PSMN4R3-80PS



Thermal characteristics 5.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	see Figure 4	-	0.3	0.49	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	Vertical in free air	-	60	-	K/W

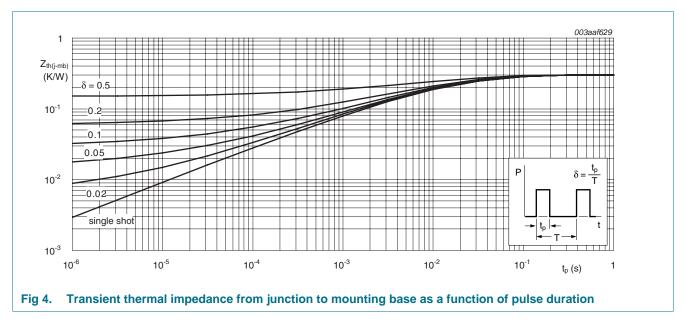


Table 5. Thermal characteristics

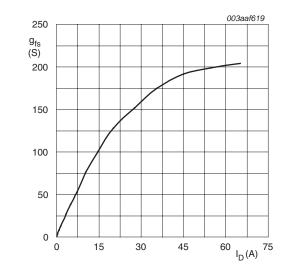
6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Static char	acteristics					
V _{(BR)DSS}	drain-source breakdown	I_D = 250 $\mu\text{A};V_{GS}$ = 0 V; T_j = -55 °C	73	-	-	V
	voltage	$I_D = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^\circ\text{C}$	80	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ see <u>Figure 10</u>	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ see <u>Figure 10</u>	-	-	4.6	V
	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 10</u> ; see <u>Figure 11</u>	2	3	4	V	
I _{DSS}	drain leakage current	V_{DS} = 80 V; V_{GS} = 0 V; T_j = 25 °C	-	0.02	10	μA
		$V_{DS} = 80 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μA
I _{GSS}	gate leakage current	V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	-	100	nA
		$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-	100	nA
R _{DSon} drain-source on-state resistance		V _{GS} = 10 V; I _D = 25 A; T _j = 175 °C; see <u>Figure 12</u>	<u>[1]</u> _	8.9	10.3	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; see <u>Figure 13</u>	[1] -	3.7	4.3	mΩ
	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 100 \text{ °C};$ see <u>Figure 12</u>	[1] -	6.1	7.1	mΩ	
R _G	internal gate resistance (AC)	f = 1 MHz	-	0.9	-	Ω
Dynamic c	haracteristics					
Q _{G(tot)}	total gate charge	$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	104	-	nC
		$I_D = 75 \text{ A}; \text{ V}_{DS} = 40 \text{ V}; \text{ V}_{GS} = 10 \text{ V};$	-	111	-	nC
Q _{GS}	gate-source charge	see Figure 14; see Figure 15	-	38	-	nC
Q _{GS(th)}	pre-threshold gate-source charge		-	24.1	-	nC
Q _{GS(th} -pl)	post-threshold gate-source charge		-	14.1	-	nC
Q _{GD}	gate-drain charge		-	28.4	-	nC
V _{GS(pl)}	gate-source plateau voltage	$I_D = 25 \text{ A}; V_{DS} = 40 \text{ V}; \text{ see } \frac{\text{Figure } 14}{\text{Figure } 15}$	-	6.1	-	V
C _{iss}	input capacitance	$V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	8161	-	pF
C _{oss}	output capacitance	$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 16}{100}$	-	701	-	pF
C _{rss}	reverse transfer capacitance		-	337	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 40 \text{ V}; \text{ R}_{L} = 0.53 \Omega; \text{ V}_{GS} = 10 \text{ V}; \label{eq:VDS}$	-	38	-	ns
t _r	rise time	$R_{G(ext)} = 4.7 \ \Omega; \ I_D = 75 \ A$	-	29	-	ns
t _{d(off)}	turn-off delay time		-	94	-	ns
t _f	fall time		-	33	-	ns

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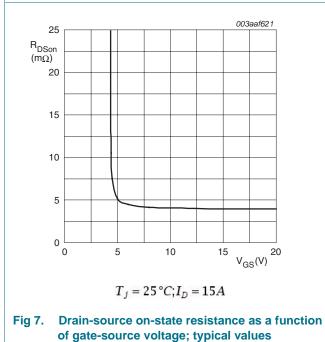
Table 6.	Characteristics continued					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Source-d	rain diode					
V_{SD}	source-drain voltage	I _S = 25 A; V _{GS} = 0 V; T _j = 25 °C; see <u>Figure 17</u>	-	-	1.2	V
t _{rr}	reverse recovery time	I _S = 25 A; dI _S /dt = 100 A/µs;	-	59	-	ns
Qr	recovered charge	$V_{GS} = 0 V; V_{DS} = 20 V$	-	109	-	nC

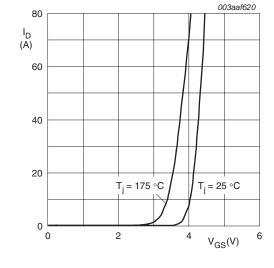
[1] Measured 3 mm from package.



 $T_j = 25 \,^{\circ}C; V_{DS} = 25V$

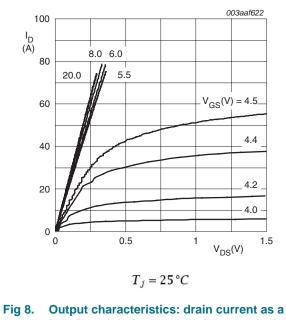










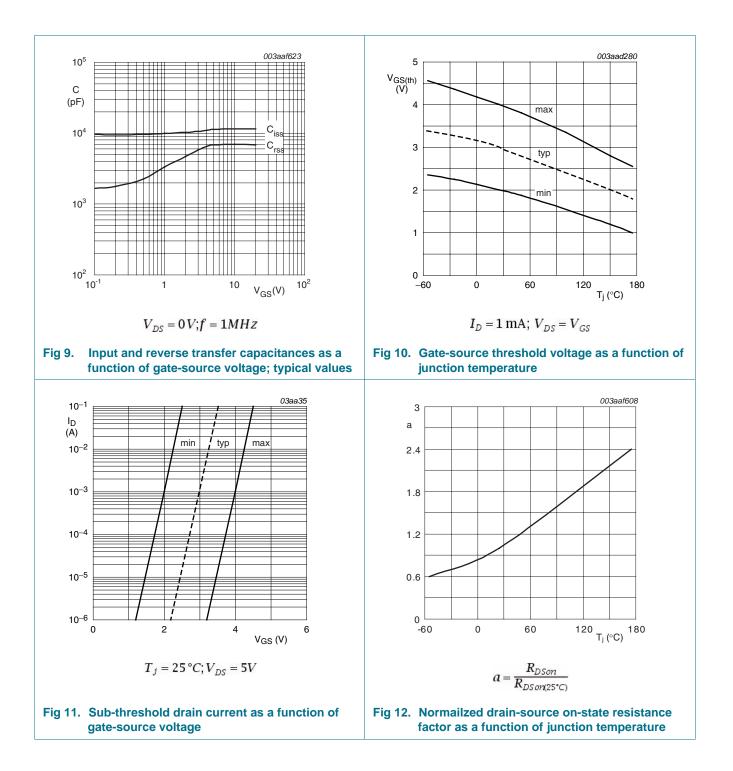


function of drain-source voltage; typical values

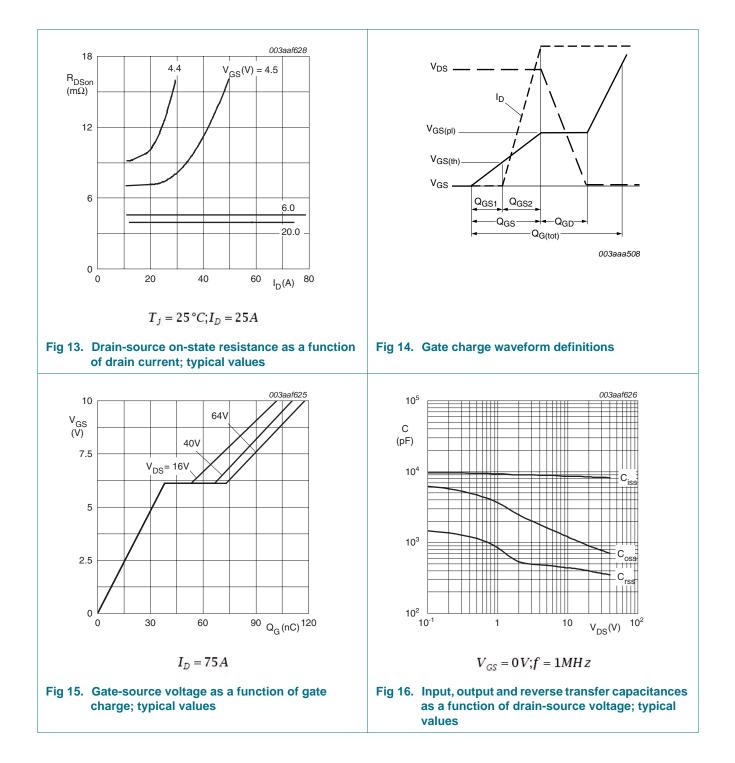
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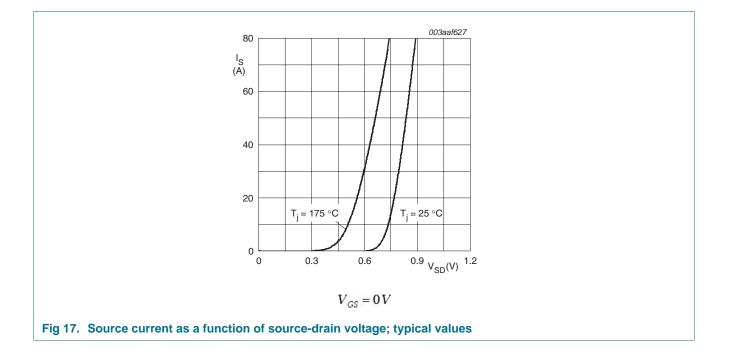
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Package outline 7.

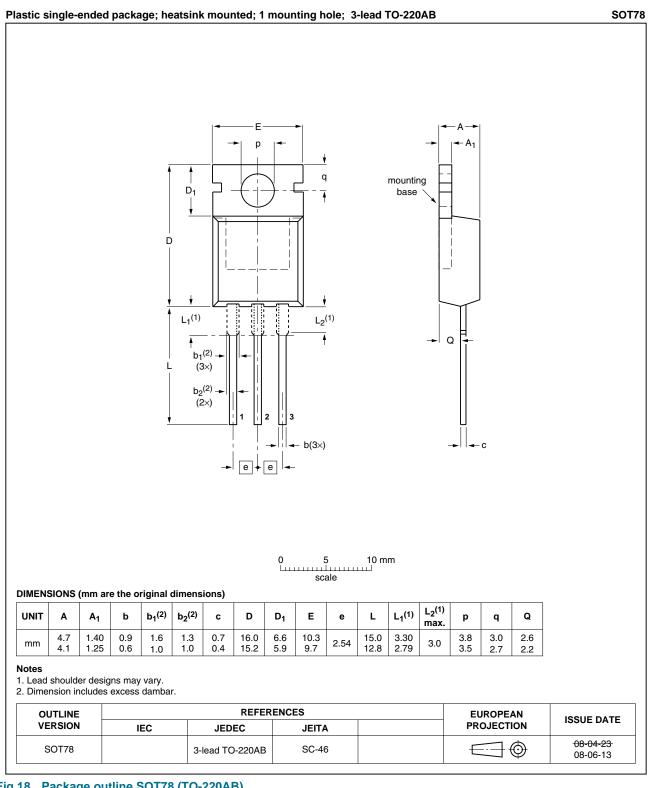


Fig 18. Package outline SOT78 (TO-220AB)

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PSMN4R3-80PS

8. Revision history

Table 7. Revision h	nistory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN4R3-80PS v.3	20110418	Product data sheet	-	PSMN4R3-80PS v.2
Modifications:	 Status change 	d from objective to product.		
	 Various chang 	jes to content.		
PSMN4R3-80PS v.2	20110309	Objective data sheet	-	PSMN4R3-80PS v.1

9. Legal information

9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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